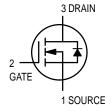
TMOS FET Transistor

N-Channel — Enhancement



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	60	Vdc
Drain–Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V _{DGR}	60	Vdc
Gate–Source Voltage — Continuous — Non–repetitive ($t_p \le 50 \mu s$)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current Continuous Pulsed	I _{DM}	200 500	mAdc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	TL	300	°C

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Drain–Source Breakdown Voltage (V _{GS} = 0, I _D = 10 μAdc)	V(BR)DSS	60	_	Vdc		
Zero Gate Voltage Drain Current (VDS = 48 Vdc, VGS = 0) (VDS = 48 Vdc, VGS = 0, TJ = 125°C)	I _{DSS}	=	1.0 1.0	μAdc mAdc		
Gate–Body Leakage Current, Forward (VGSF = 15 Vdc, VDS = 0)	IGSSF	_	-10	nAdc		
ON CHARACTERISTICS ⁽¹⁾	ON CHARACTERISTICS(1)					
Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.0 mAdc)	VGS(th)	0.8	3.0	Vdc		
Static Drain–Source On–Resistance (VGS = 10 Vdc, I_D = 0.5 Adc) (VGS = 4.5 Vdc, I_D = 75 mAdc)	^r DS(on)		5.0 6.0	Ohm		
Drain-Source On-Voltage (V _{GS} = 10 Vdc, I _D = 0.5 Adc) (V _{GS} = 4.5 Vdc, I _D = 75 mAdc)	V _{DS(on)}	_ _	2.5 0.45	Vdc		

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 3

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Motorola Preferred Device



ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted) (Continued)

Ch	Symbol	Min	Max	Unit	
ON CHARACTERISTICS ⁽¹⁾ (continued)					
On-State Drain Current (VGS = 4.5 Vdc, VDS = 10 Vdc)		I _{d(on)}	75	_	mAdc
Forward Transconductance (VDS = 10 Vdc, ID = 200 mAd	9fs	100	_	μmhos	
DYNAMIC CHARACTERISTICS					
Input Capacitance		C _{iss}	_	60	pF
Output Capacitance	$(V_{DS} = 25 \text{ V}, V_{GS} = 0, \\ f = 1.0 \text{ MHz})$	C _{oss}	_	25	
Reverse Transfer Capacitance	- ,	C _{rss}	_	5.0	
SWITCHING CHARACTERISTICS(1)					
Turn-On Delay Time	(V _{DD} = 15 V, I _D = 500 mA,	t _{on}	_	10	ns
Turn-Off Delay Time	$R_{gen} = 25 \text{ ohms}, R_L = 25 \text{ ohms})$	toff	_	10	

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

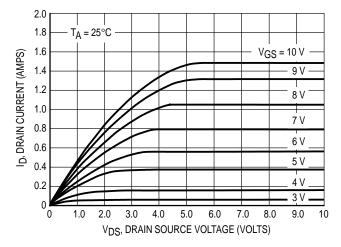


Figure 1. Ohmic Region

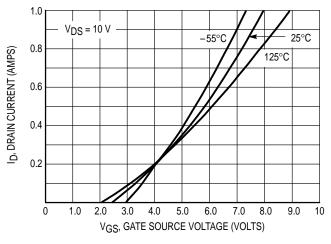


Figure 2. Transfer Characteristics

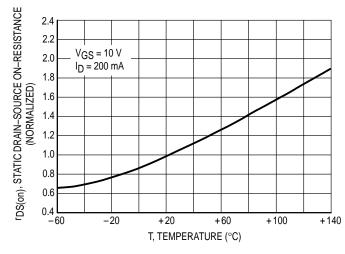


Figure 3. Temperature versus Static Drain–Source On–Resistance

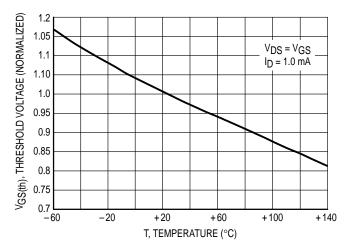
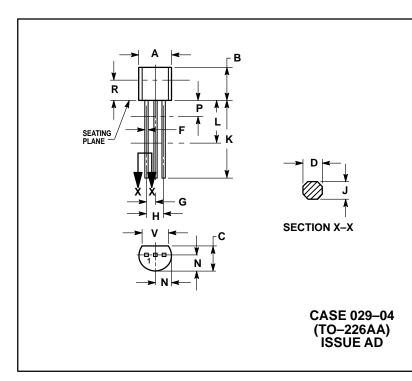


Figure 4. Temperature versus Gate Threshold Voltage

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
7	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3 43	

STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

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